PrimePACK™3+ B-series module with TRENCHSTOP™IGBT7 and emitter controlled 7 diode and NTC

Features

- Electrical features
  - V_{CES} = 1200 V
  - $I_{C\ nom}$ = 2400 A / I_{CRM} = 4800 A
  - High current density
  - Low inductive design
  - Low $V_{CE,sat}$
  - $T_{vj,op}$ = 150°C
  - Overload operation up to 175°C
- Mechanical features
  - 4 kV AC 1 min insulation
  - High creepage and clearance distances
  - High power density

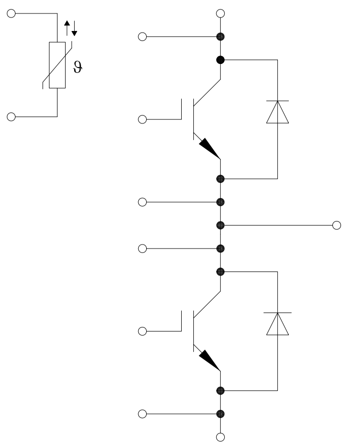
Potential applications

- Motor drives

Product validation

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

Description



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1 Package

Table 1 Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	V_{ISOL}	RMS, f = 50 Hz, t = 60 s	4.0	kV
Material of module baseplate			Cu	
Internal isolation		basic insulation (class 1, IEC 61140)	Al_2O_3	
Creepage distance	d_{Creep}	terminal to heatsink	36.0	mm
Creepage distance	d_{Creep}	terminal to terminal	28.0	mm
Clearance	d_{Clear}	terminal to heatsink	21.0	mm
Clearance	d_{Clear}	terminal to terminal	19.0	mm
Comparative tracking index	CTI		> 400	

Table 2 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Stray inductance module	L_{sCE}				10		nH
Module lead resistance, terminals - chip	$R_{AA'+CC'}$	T_C = 25 °C, per switch			0.1		mΩ
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	T_C = 25 °C, per switch			0.135		mΩ
Current slope at AC-terminals	$\|di/dt_{AC}\|$	Valid if AC-terminals are permanently part of commutation path				100	A/µs
Storage temperature	T_{stg}			-40		150	°C
Maximum baseplate operation temperature	T_{BPmax}					150	°C
Mounting torque for module mounting	M	- Mounting according to valid application note	M5, Screw	3		6	Nm
Terminal connection torque	M	- Mounting according to valid application note	M4, Screw	1.8		2.1	Nm
			M8, Screw	8		10	
Weight	G				1400		g

2 IGBT, Inverter

Table 3 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Collector-emitter voltage	V_{CES}		T_{vj} = 25 °C	1200	V

(table continues...)

Table 3 **(continued) Maximum rated values**

Parameter	Symbol	Note or test condition		Values	Unit
Implemented collector current	I_{CN}			2400	A
Continuous DC collector current	I_{CDC}	$T_{vj\,max}$ = 175 °C	T_C = 95 °C	2400	A
Repetitive peak collector current	I_{CRM}	t_p limited by $T_{vj\,op}$		4800	A
Gate-emitter peak voltage	V_{GES}			±20	V

Table 4 **Characteristic values**

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE\,sat}$	I_C = 2400 A, V_{GE} = 15 V	T_{vj} = 25 °C		1.27	1.79	V
			T_{vj} = 125 °C		1.37	1.82	
			T_{vj} = 175 °C		1.43	1.85	
Gate threshold voltage	V_{GEth}	I_C = 48 mA, V_{CE} = V_{GE}, T_{vj} = 25 °C		5.15	5.80	6.45	V
Gate charge	Q_G	V_{GE} = ±15 V, V_{CC} = 600 V			38.1		µC
Internal gate resistor	R_{Gint}	T_{vj} = 25 °C			0.33		Ω
Input capacitance	C_{ies}	f = 100 kHz, T_{vj} = 25 °C, V_{CE} = 25 V, V_{GE} = 0 V			325		nF
Reverse transfer capacitance	C_{res}	f = 100 kHz, T_{vj} = 25 °C, V_{CE} = 25 V, V_{GE} = 0 V			1.92		nF
Collector-emitter cut-off current	I_{CES}	V_{CE} = 1200 V, V_{GE} = 0 V	T_{vj} = 25 °C			5	mA
Gate-emitter leakage current	I_{GES}	V_{CE} = 0 V, V_{GE} = 20 V, T_{vj} = 25 °C				400	nA
Turn-on delay time (inductive load)	t_{don}	I_C = 2400 A, V_{CC} = 600 V, V_{GE} = ±15 V, R_{Gon} = 0.2 Ω	T_{vj} = 25 °C		0.790		µs
			T_{vj} = 125 °C		0.840		
			T_{vj} = 175 °C		0.870		
Rise time (inductive load)	t_r	I_C = 2400 A, V_{CC} = 600 V, V_{GE} = ±15 V, R_{Gon} = 0.2 Ω	T_{vj} = 25 °C		0.120		µs
			T_{vj} = 125 °C		0.140		
			T_{vj} = 175 °C		0.150		
Turn-off delay time (inductive load)	t_{doff}	I_C = 2400 A, V_{CC} = 600 V, V_{GE} = ±15 V, R_{Goff} = 0.4 Ω	T_{vj} = 25 °C		0.940		µs
			T_{vj} = 125 °C		1.060		
			T_{vj} = 175 °C		1.120		
Fall time (inductive load)	t_f	I_C = 2400 A, V_{CC} = 600 V, V_{GE} = ±15 V, R_{Goff} = 0.4 Ω	T_{vj} = 25 °C		0.230		µs
			T_{vj} = 125 °C		0.430		
			T_{vj} = 175 °C		0.530		

(table continues...)

Table 4 (continued) Characteristic values

Parameter	Symbol	Note or test condition		Values Min.	Values Typ.	Values Max.	Unit
Turn-on energy loss per pulse	E_{on}	I_C = 2400 A, V_{CC} = 600 V, L_σ = 20 nH, V_{GE} = ±15 V, R_{Gon} = 0.2 Ω, di/dt = 15500 A/µs (T_{vj} = 175 °C)	T_{vj} = 25 °C		200		mJ
			T_{vj} = 125 °C		295		
			T_{vj} = 175 °C		380		
Turn-off energy loss per pulse	E_{off}	I_C = 2400 A, V_{CC} = 600 V, L_σ = 20 nH, V_{GE} = ±15 V, R_{Goff} = 0.4 Ω, dv/dt = 2200 V/µs (T_{vj} = 175 °C)	T_{vj} = 25 °C		355		mJ
			T_{vj} = 125 °C		510		
			T_{vj} = 175 °C		570		
SC data	I_{SC}	V_{GE} = 15 V, V_{CC} = 800 V, V_{CEmax}=V_{CES}-L_{sCE}*di/dt	t_P = 6 µs, T_{vj} = 150 °C		8500		A
			t_P = 6 µs, T_{vj} = 175 °C		8000		
Thermal resistance, junction to case	R_{thJC}	per IGBT				17.9	K/kW
Thermal resistance, case to heat sink	R_{thCH}	per IGBT, λ_{grease} = 1 W/(m·K)			12.9		K/kW
Temperature under switching conditions	$T_{vj\,op}$			-40		175	°C

Note: *Maximum RMS module DC-terminal current according to application note AN2009-08.*
Tvj op > 150 °C is only allowed for operation at overload conditions. For detailed specifications please refer to AN2018-14.

3 Diode, Inverter

Table 5 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Repetitive peak reverse voltage	V_{RRM}		T_{vj} = 25 °C	1200	V
Continuous DC forward current	I_F			2400	A
Repetitive peak forward current	I_{FRM}	t_P = 1 ms		4800	A
I^2t - value	I^2t	t_P = 10 ms, V_R = 0 V	T_{vj} = 125 °C	455	kA^2s
			T_{vj} = 175 °C	420	

Table 6 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Forward voltage	V_F	I_F = 2400 A, V_{GE} = 0 V	T_{vj} = 25 °C		1.70	2.03	V
			T_{vj} = 125 °C		1.65	1.96	
			T_{vj} = 175 °C		1.55	1.91	
Peak reverse recovery current	I_{RM}	V_{CC} = 600 V, I_F = 2400 A, V_{GE} = -15 V, -di$_F$/dt = 15500 A/µs (T_{vj} = 175 °C)	T_{vj} = 25 °C		1410		A
			T_{vj} = 125 °C		1720		
			T_{vj} = 175 °C		1850		
Recovered charge	Q_r	V_{CC} = 600 V, I_F = 2400 A, V_{GE} = -15 V, -di$_F$/dt = 15500 A/µs (T_{vj} = 175 °C)	T_{vj} = 25 °C		265		µC
			T_{vj} = 125 °C		455		
			T_{vj} = 175 °C		585		
Reverse recovery energy	E_{rec}	V_{CC} = 600 V, I_F = 2400 A, V_{GE} = -15 V, -di$_F$/dt = 15500 A/µs (T_{vj} = 175 °C)	T_{vj} = 25 °C		110		mJ
			T_{vj} = 125 °C		200		
			T_{vj} = 175 °C		250		
Thermal resistance, junction to case	R_{thJC}	per diode				34.1	K/kW
Thermal resistance, case to heat sink	R_{thCH}	per diode, λ_{grease} = 1 W/(m·K)			14.7		K/kW
Temperature under switching conditions	$T_{vj\,op}$			-40		175	°C

Note: *Tvj op > 150 °C is only allowed for operation at overload conditions. For detailed specifications please refer to AN2018-14.*

4 NTC-Thermistor

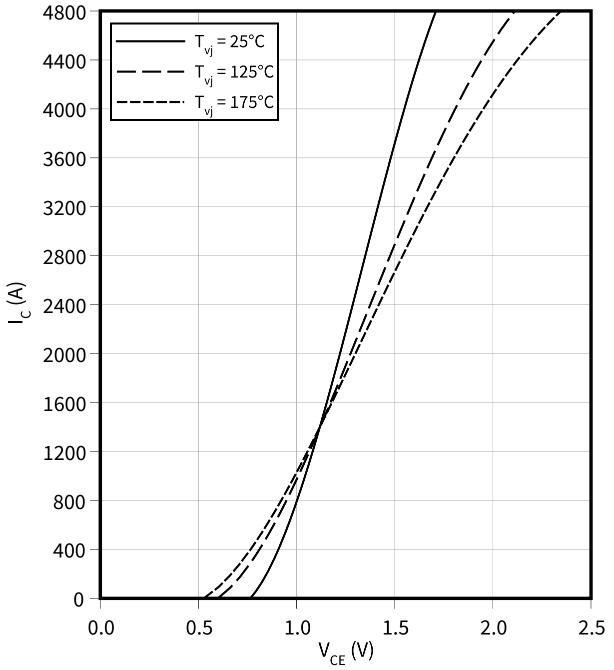
Table 7 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Rated resistance	R_{25}	T_{NTC} = 25 °C		5		kΩ
Deviation of R_{100}	$\Delta R/R$	T_{NTC} = 100 °C, R_{100} = 493 Ω	-5		5	%
Power dissipation	P_{25}	T_{NTC} = 25 °C			20	mW
B-value	$B_{25/50}$	$R_2 = R_{25}\exp[B_{25/50}(1/T_2-1/(298,15\ K))]$		3375		K
B-value	$B_{25/80}$	$R_2 = R_{25}\exp[B_{25/80}(1/T_2-1/(298,15\ K))]$		3411		K
B-value	$B_{25/100}$	$R_2 = R_{25}\exp[B_{25/100}(1/T_2-1/(298,15\ K))]$		3433		K

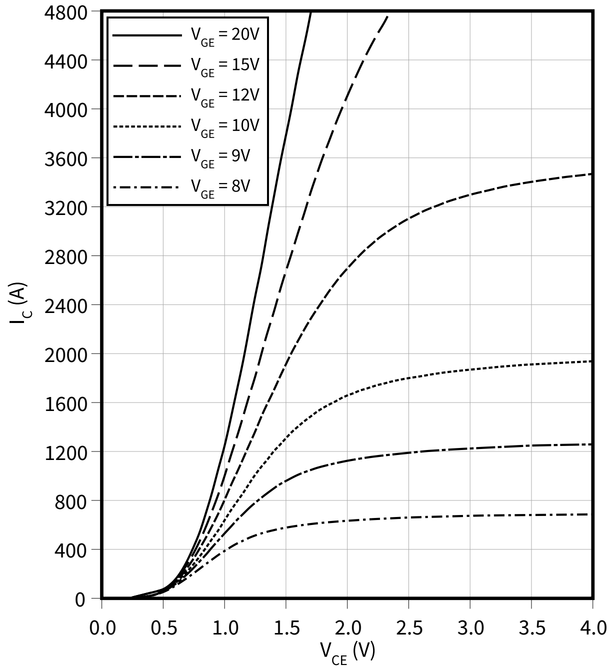
Note: *For an analytical description of the NTC characteristics please refer to AN2009-10, chapter 4*

5 Characteristics diagrams

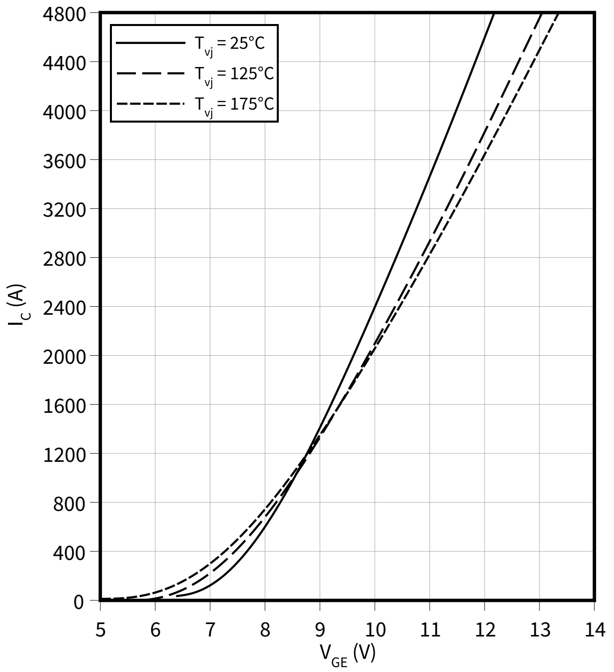
Output characteristic (typical), IGBT, Inverter
$I_C = f(V_{CE})$
$V_{GE} = 15$ V



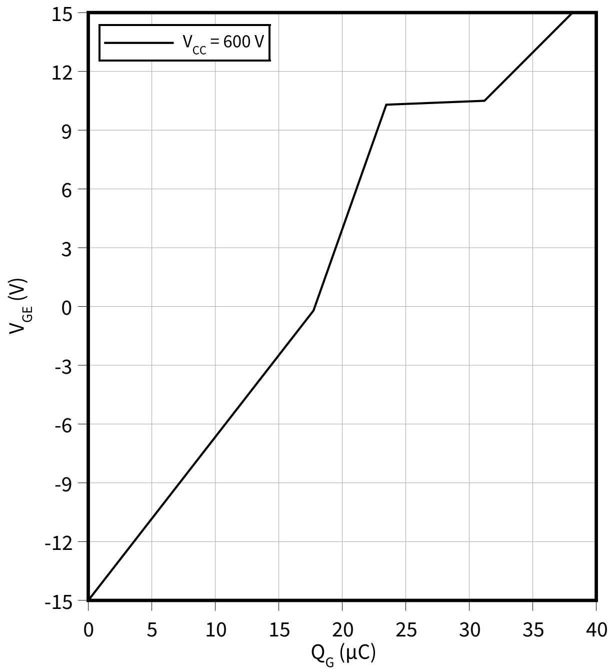
Output characteristic field (typical), IGBT, Inverter
$I_C = f(V_{CE})$
$T_{vj} = 175$ °C



Transfer characteristic (typical), IGBT, Inverter
$I_C = f(V_{GE})$
$V_{CE} = 20$ V



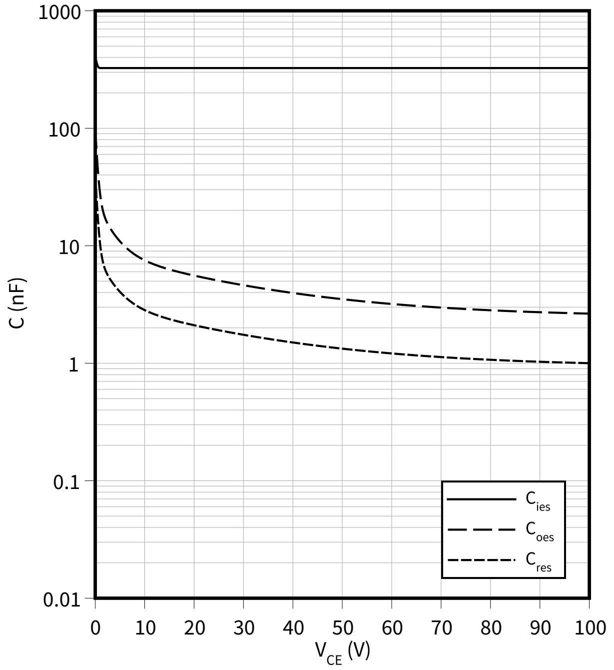
Gate charge characteristic (typical), IGBT, Inverter
$V_{GE} = f(Q_G)$
$I_C = 2400$ A, $T_{vj} = 25$ °C



Capacity characteristic (typical), IGBT, Inverter

$C = f(V_{CE})$

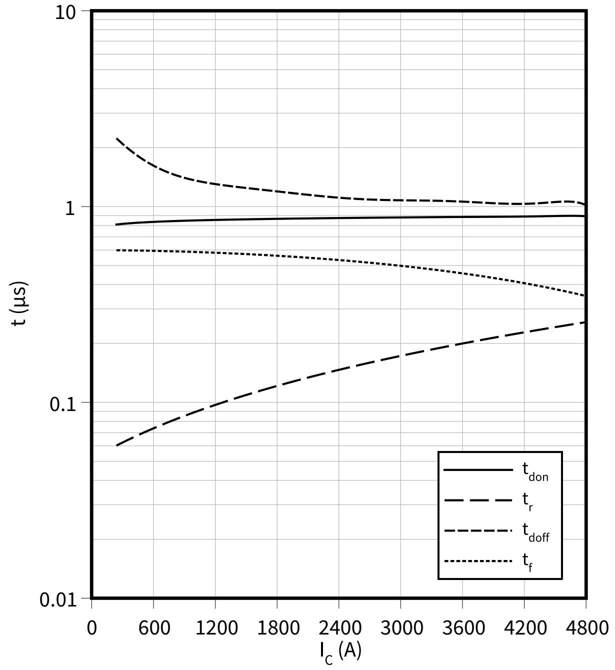
$f = 100\ kHz$, $V_{GE} = 0\ V$, $T_{vj} = 25\ °C$



Switching times (typical), IGBT, Inverter

$t = f(I_C)$

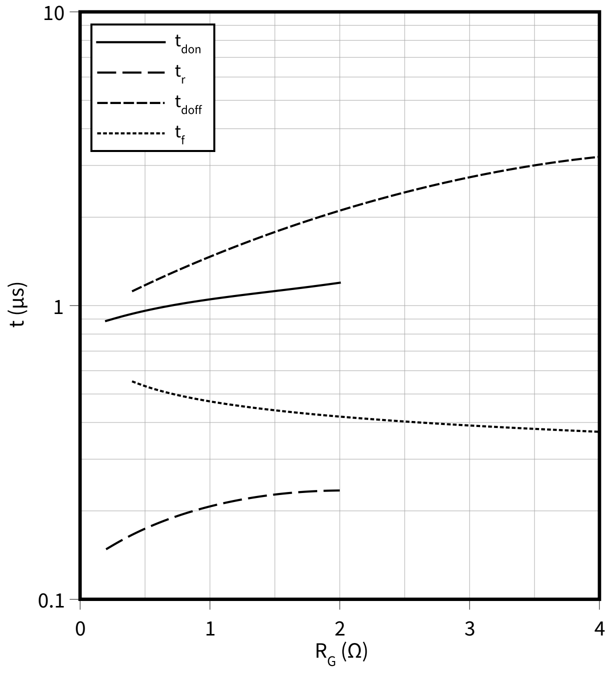
$R_{Goff} = 0.4\ \Omega$, $R_{Gon} = 0.2\ \Omega$, $V_{CC} = 600\ V$, $V_{GE} = \pm 15\ V$, $T_{vj} = 175\ °C$



Switching times (typical), IGBT, Inverter

$t = f(R_G)$

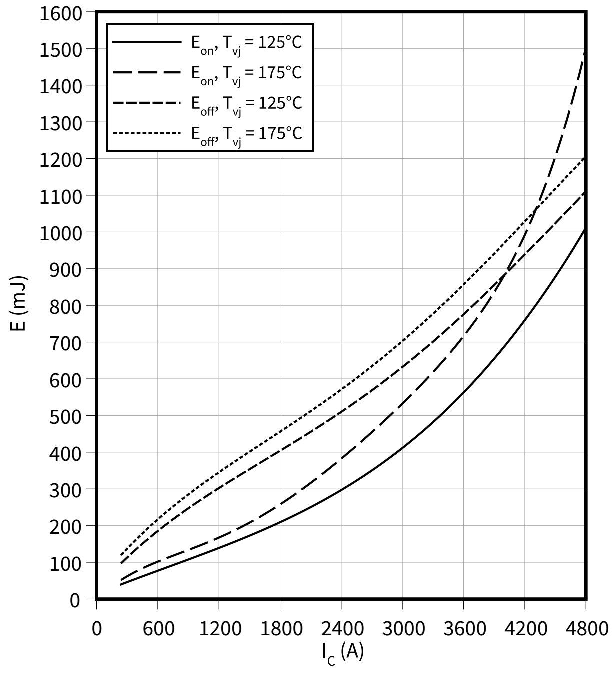
$I_C = 2400\ A$, $V_{CC} = 600\ V$, $V_{GE} = \pm 15\ V$, $T_{vj} = 175\ °C$



Switching losses (typical), IGBT, Inverter

$E = f(I_C)$

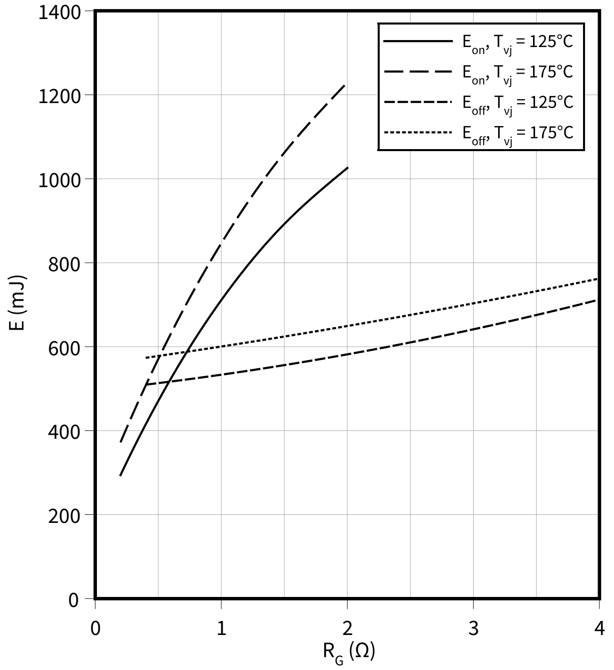
$R_{Goff} = 0.4\ \Omega$, $R_{Gon} = 0.2\ \Omega$, $V_{CC} = 600\ V$, $V_{GE} = \pm 15\ V$



Switching losses (typical), IGBT, Inverter

$E = f(R_G)$

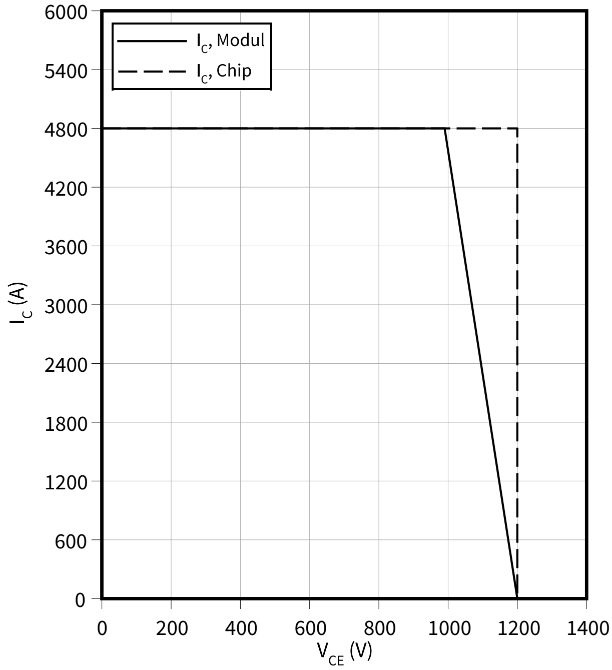
$I_C = 2400$ A, $V_{CC} = 600$ V, $V_{GE} = \pm 15$ V



Reverse bias safe operating area (RBSOA), IGBT, Inverter

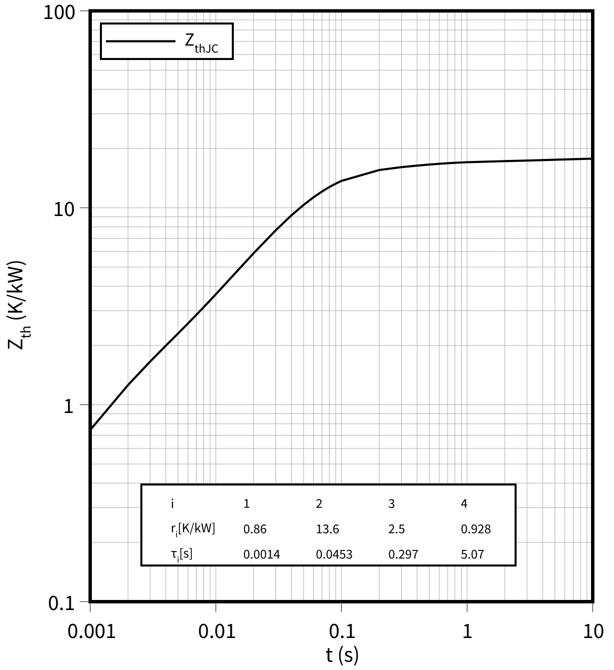
$I_C = f(V_{CE})$

$R_{Goff} = 0.4\ \Omega$, $V_{GE} = 15$ V, $T_{vj} = 175$ °C



Transient thermal impedance, IGBT, Inverter

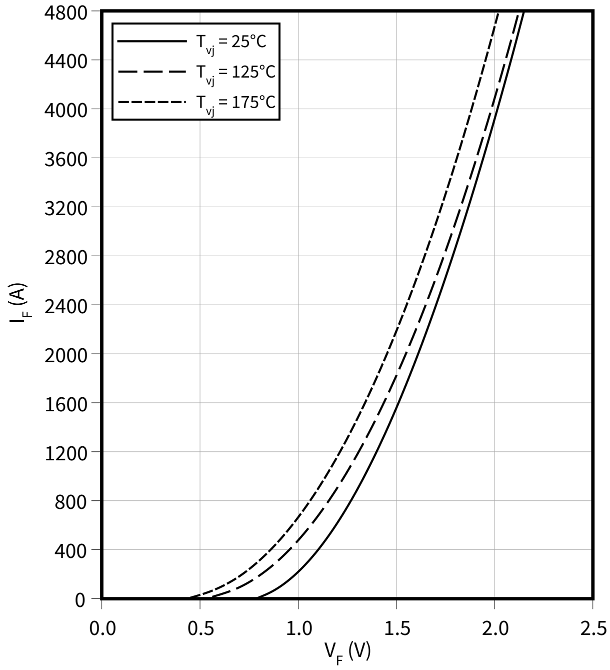
$Z_{th} = f(t)$



i	1	2	3	4
r_i[K/kW]	0.86	13.6	2.5	0.928
τ_i[s]	0.0014	0.0453	0.297	5.07

Forward characteristic (typical), Diode, Inverter

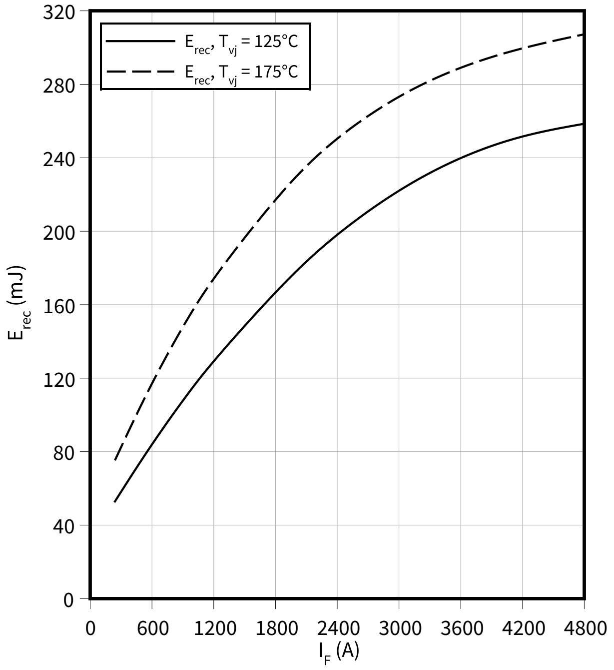
$I_F = f(V_F)$



Switching losses (typical), Diode, Inverter

$E_{rec} = f(I_F)$

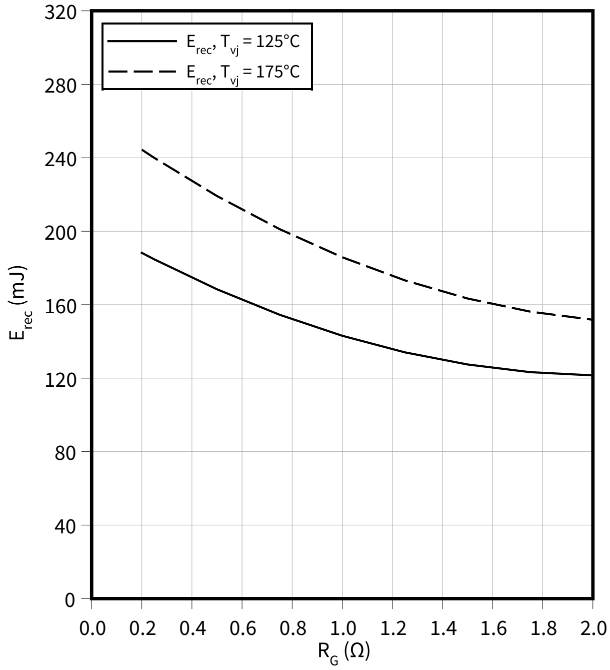
$V_{CE} = 600$ V, $R_{Gon} = R_{Gon}$(IGBT)



Switching losses (typical), Diode, Inverter

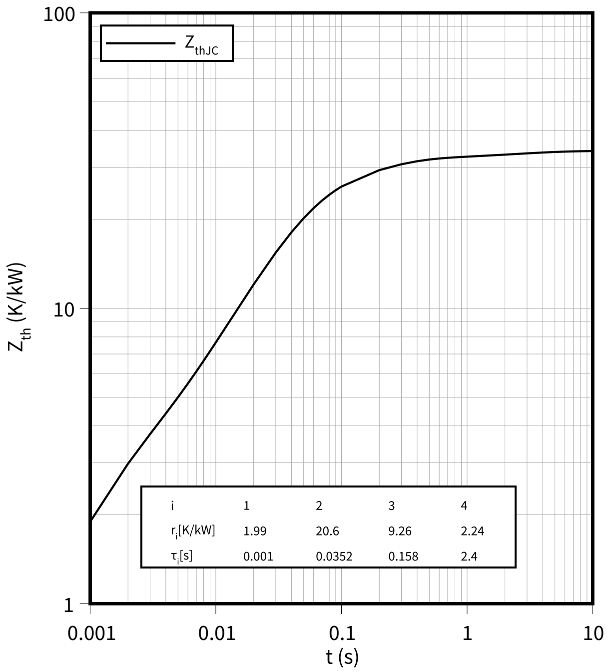
$E_{rec} = f(R_G)$

$V_{CE} = 600$ V, $I_F = 2400$ A



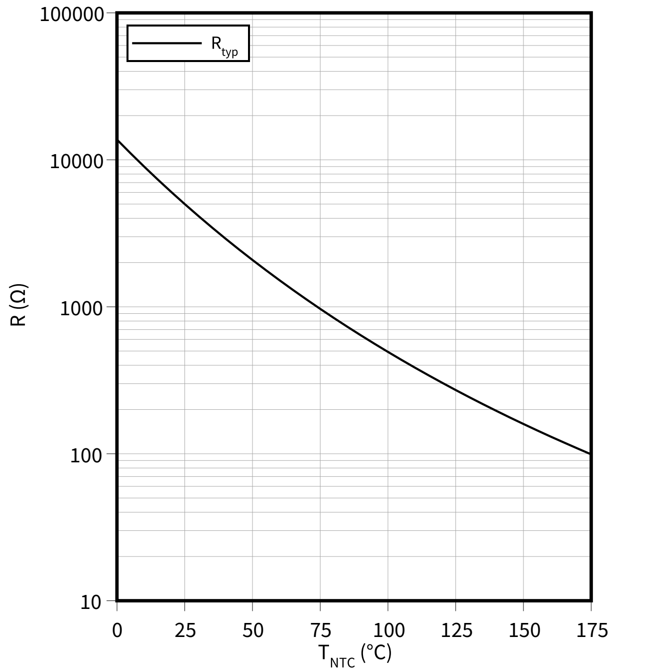
Transient thermal impedance, Diode, Inverter

$Z_{th} = f(t)$



Temperature characteristic (typical), NTC-Thermistor

$R = f(T_{NTC})$



6 Circuit diagram

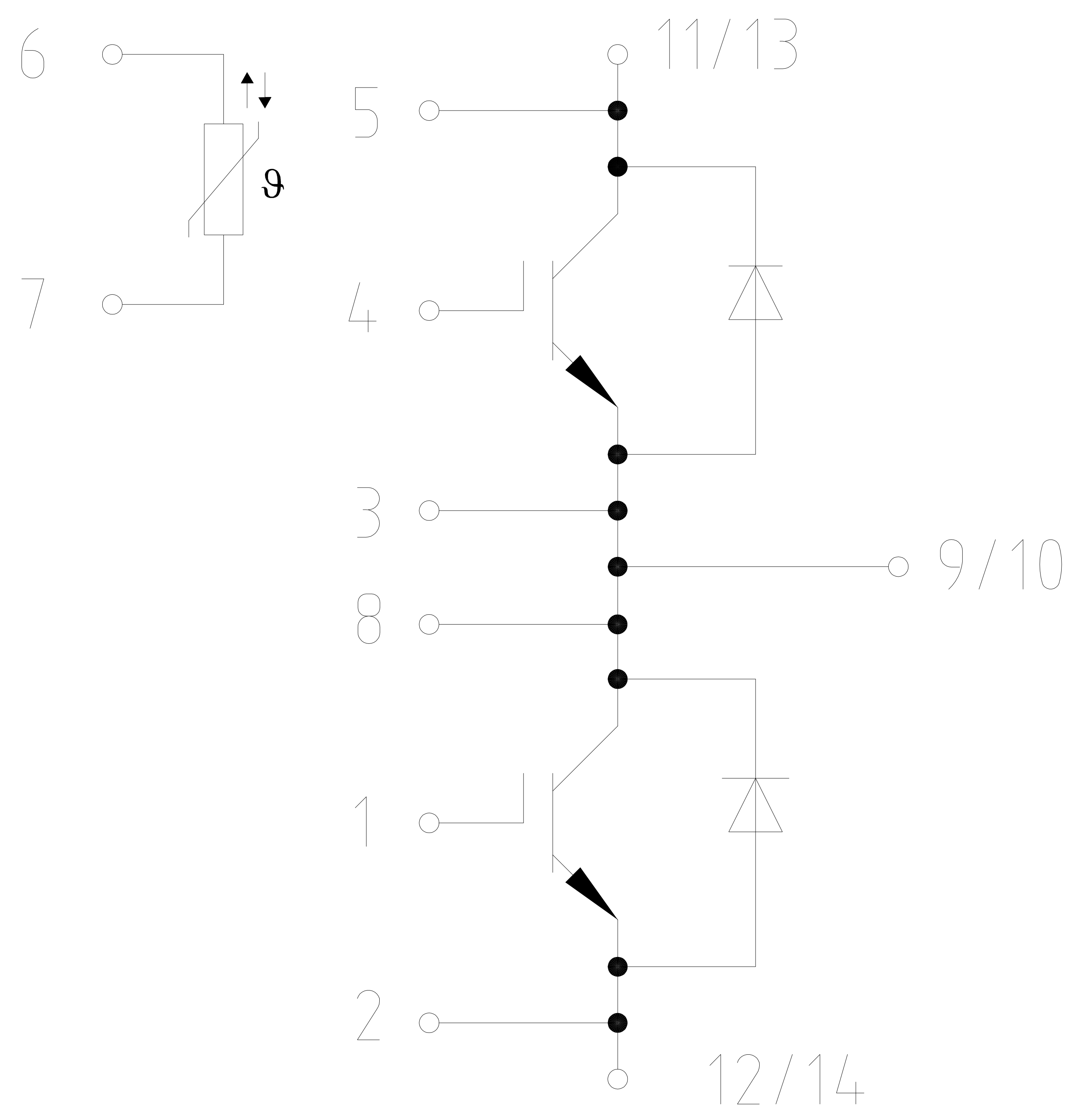


Figure 1

7 Package outlines

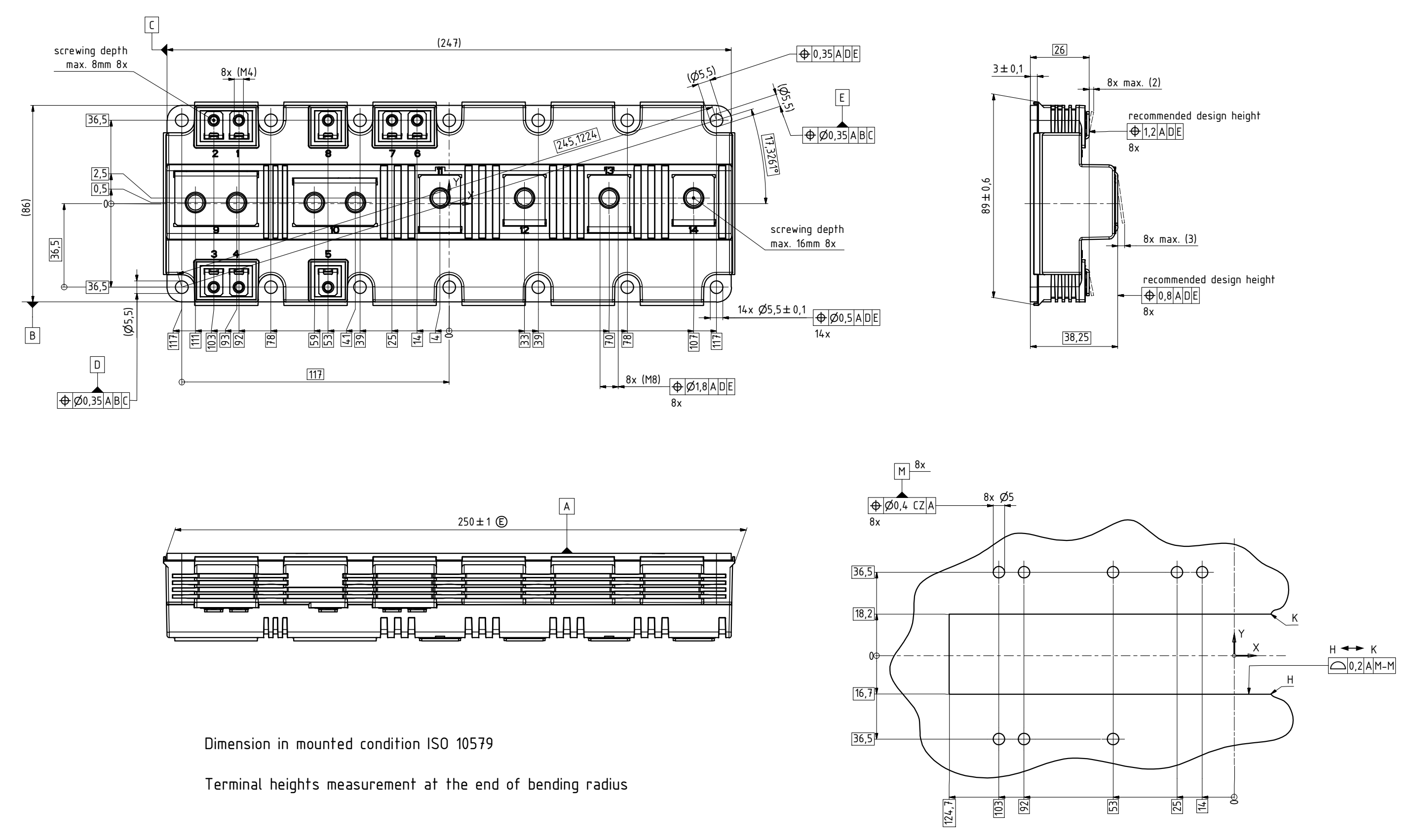


Figure 2

8 Module label code

Module label code		
Code format	Data Matrix	Barcode Code128
Encoding	ASCII text	Code Set A
Symbol size	16x16	23 digits
Standard	IEC24720 and IEC16022	IEC8859-1

Code content	*Content* Module serial number Module material number Production order number Date code (production year) Date code (production week)	*Digit* 1 – 5 6 - 11 12 - 19 20 – 21 22 – 23	*Example* 71549 142846 55054991 15 30
Example	71549142846550549911530		71549142846550549911530

Figure 3

Revision history

Document revision	Date of release	Description of changes
0.10	2021-11-09	Initial version
0.20	2022-10-28	Target datasheet
1.00	2023-06-09	Final datasheet

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